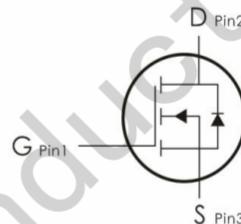
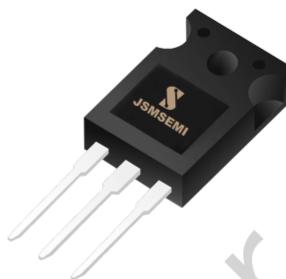


FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information		
Device	Package	Marking
FQA62N25C	TO-247	FQA62N25C

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted			
Parameter	Symbol	Value	Unit
		TO-247	
Drain-Source Voltage	V_{DSS}	250	V
Continuous Drain Current	I_D	60	A
Pulsed Drain Current (note2)	I_{DM}	240	A
Gate-Source Voltage	V_{GSS}	± 20	V
Single Pulse Avalanche Energy (note2)	E_{AS}	780	mJ
Avalanche Current (note1)	I_{AR}	39.5	V/ns
Repetitive Avalanche Energy (note1)	E_{AR}	468	mJ
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	400	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 175	$^\circ\text{C}$

Thermal Resistance			
Parameter	Symbol	Value	Unit
		TO-247	
Thermal Resistance, Junction-to-Case	R_{thJC}	0.5	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	45	

Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	250	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = 250\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 25^\circ\text{C}$	--	--	1	μA
Gate-Source Leakage	I_{GSS}	$V_{\text{GS}} = +20\text{V}, V_{\text{DS}} = 0\text{V}$	--	--	100	nA
		$V_{\text{GS}} = -20\text{V}, V_{\text{DS}} = 0\text{V}$	--	--	-100	
Gate-Source Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	2.0	--	4.0	V
Drain-Source On-Resistance (Note3)	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10\text{V}, I_D = 25\text{A}$	--	30	48	$\text{m}\Omega$
Dynamic						
Input Capacitance	C_{iss}	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 25\text{V}, f = 1.0\text{MHz}$	--	3538	--	pF
Output Capacitance	C_{oss}		--	657	--	
Reverse Transfer Capacitance	C_{rss}		--	280	--	
Total Gate Charge	Q_g	$V_{\text{DD}} = 160\text{V}, I_D = 25\text{A}, V_{\text{GS}} = 0 \text{ to } 10\text{V}$	--	244	--	nC
Gate-Source Charge	Q_{gs}		--	16	--	
Gate-Drain Charge	Q_{gd}		--	144	--	
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = 100\text{V}, I_D = 25\text{A}, V_{\text{GS}} = 10\text{V} R_G = 25 \Omega$	--	53	--	ns
Turn-on Rise Time	t_r		--	65	--	
Turn-off Delay Time	$t_{\text{d}(\text{off})}$		--	689	--	
Turn-off Fall Time	t_f		--	230	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^\circ\text{C}$	--	--	60	A
Pulsed Diode Forward Current	I_{SM}		--	--	240	
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{\text{SD}} = 25\text{A}, V_{\text{GS}} = 0\text{V}$	--	--	1.5	V
Reverse Recovery Time	t_{rr}	$V_{\text{GS}} = 0\text{V}, I_S = 25\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	--	208	--	ns
Reverse Recovery Charge	Q_{rr}		--	2.04	--	μC

Notes

- Repetitive Rating: Pulse width limited by maximum junction temperature
- $I_{\text{AS}} = 30\text{A}, V_{\text{DD}} = 30\text{V}, R_G = 25 \Omega$, Starting $T_J = 25^\circ\text{C}$
- Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 1\%$

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics ($T_J = 25^\circ\text{C}$)

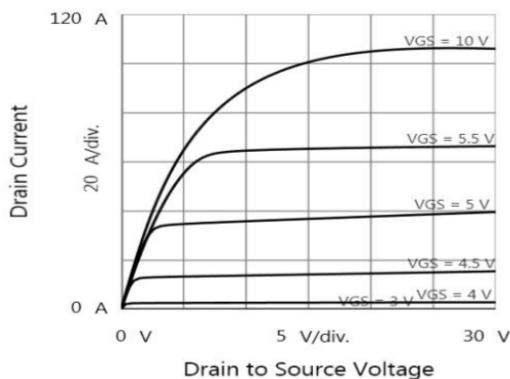


Figure 2. Transfer Characteristics

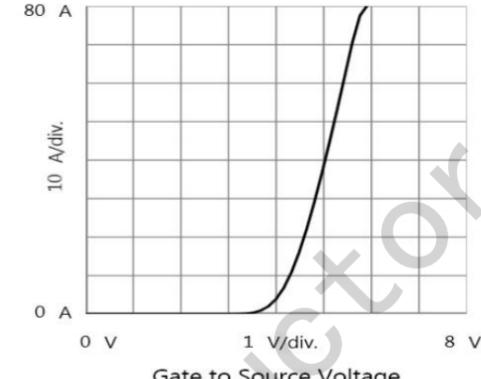


Figure 3. Maximum Continuous Drain Current vs Case Temperature

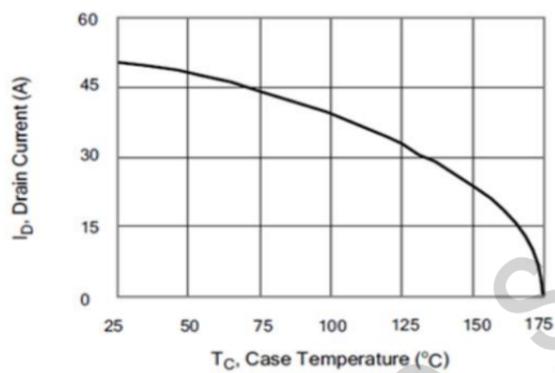


Figure 4. Drain to Source Voltage vs. Gate to Source Voltage

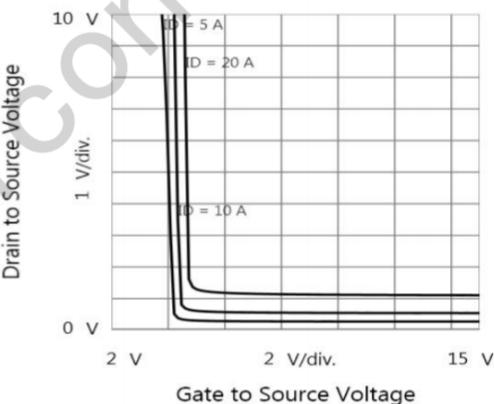


Figure 5 . Typical Breakdown Voltage vs Junction Temperature

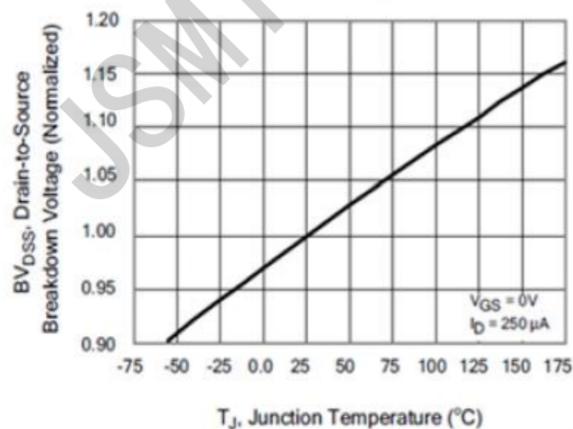
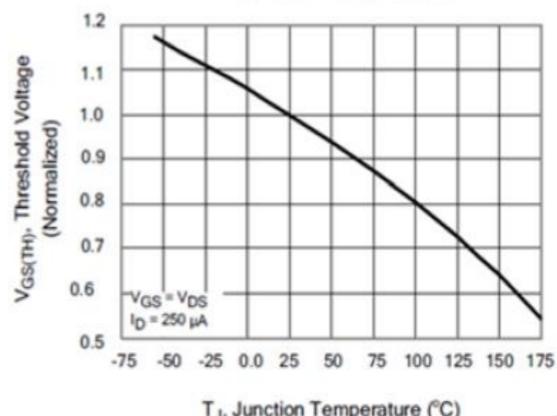


Figure 6 . Typical Threshold Voltage vs Junction Temperature



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Capacitance

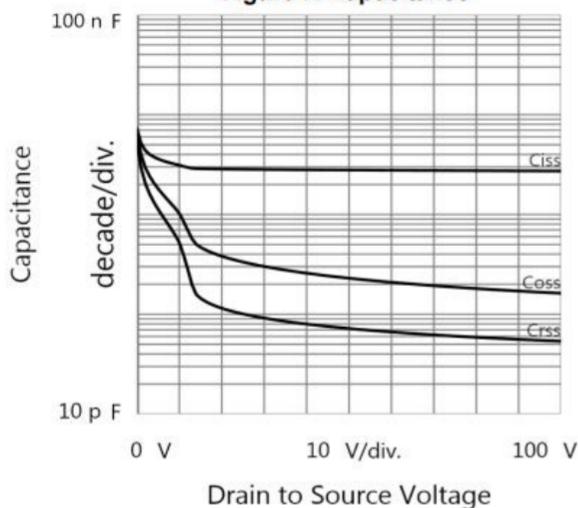


Figure 8. Gate Charge

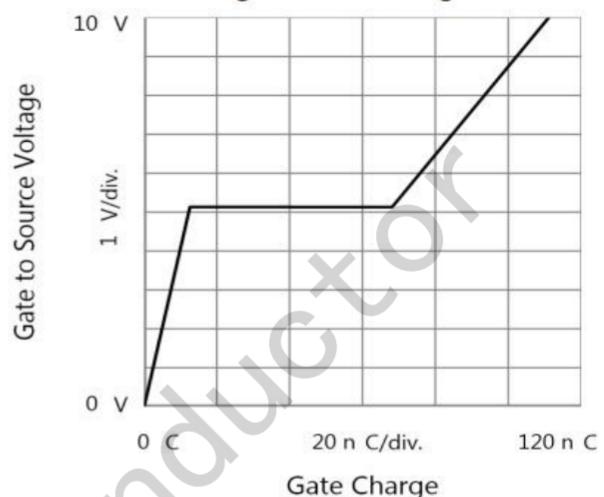


Figure 9. Transient Thermal Impedance
 TO-247, TO-3P

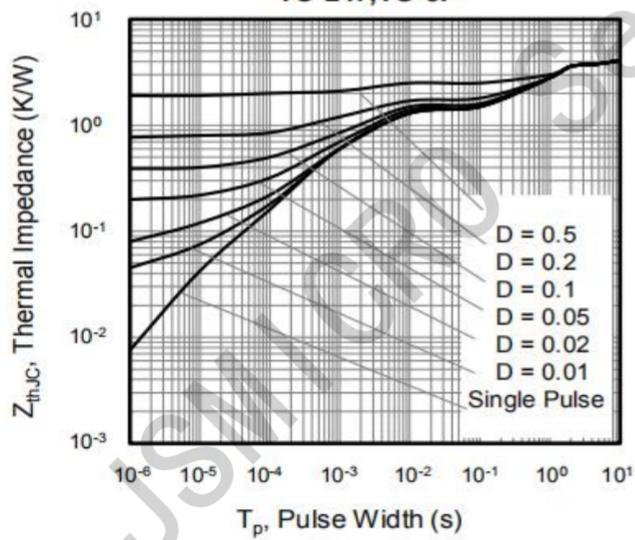


Figure 10. Maximum Forward Bias Safe Operating Area

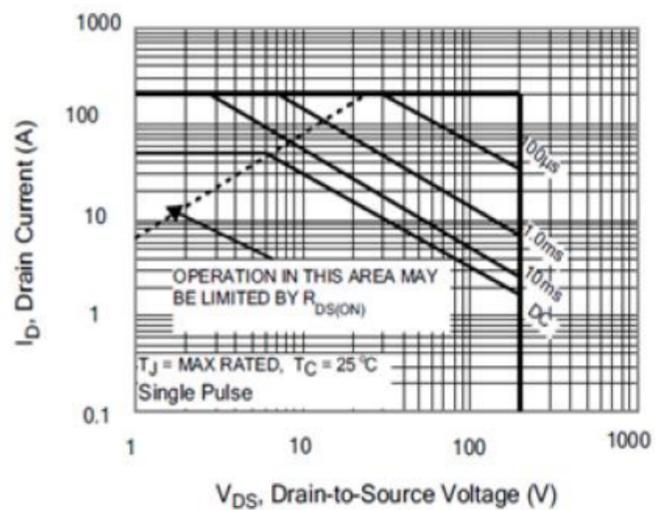
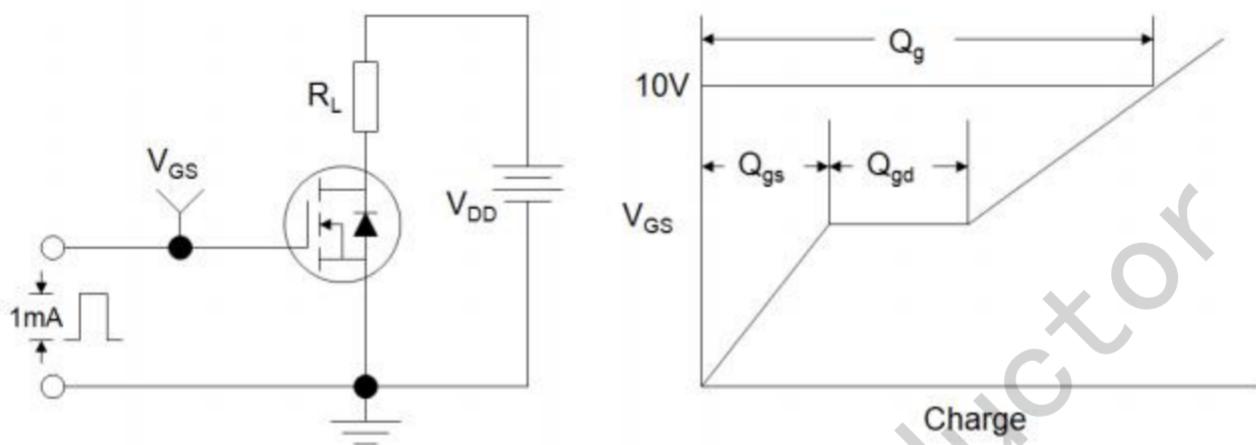
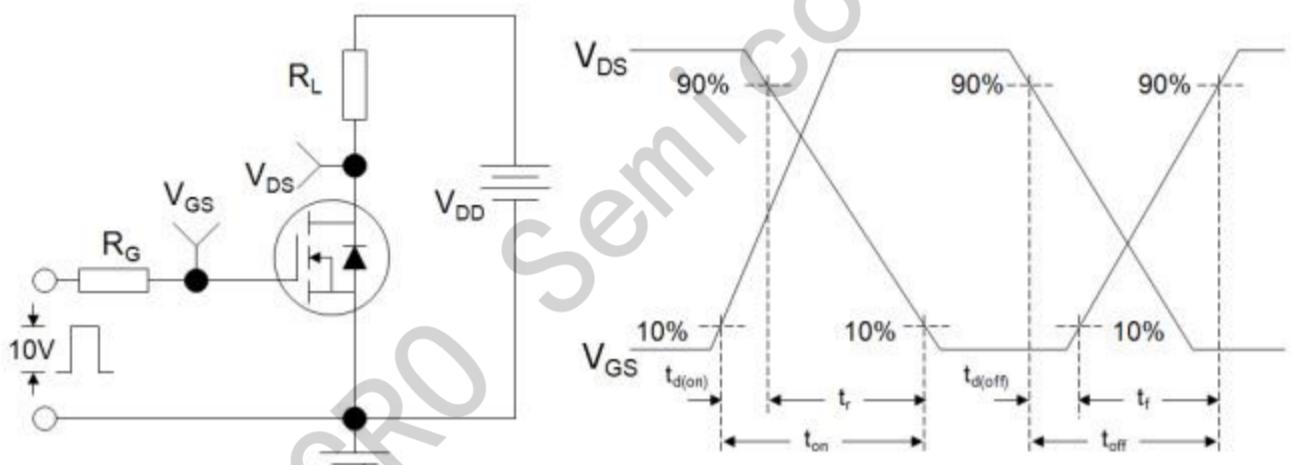
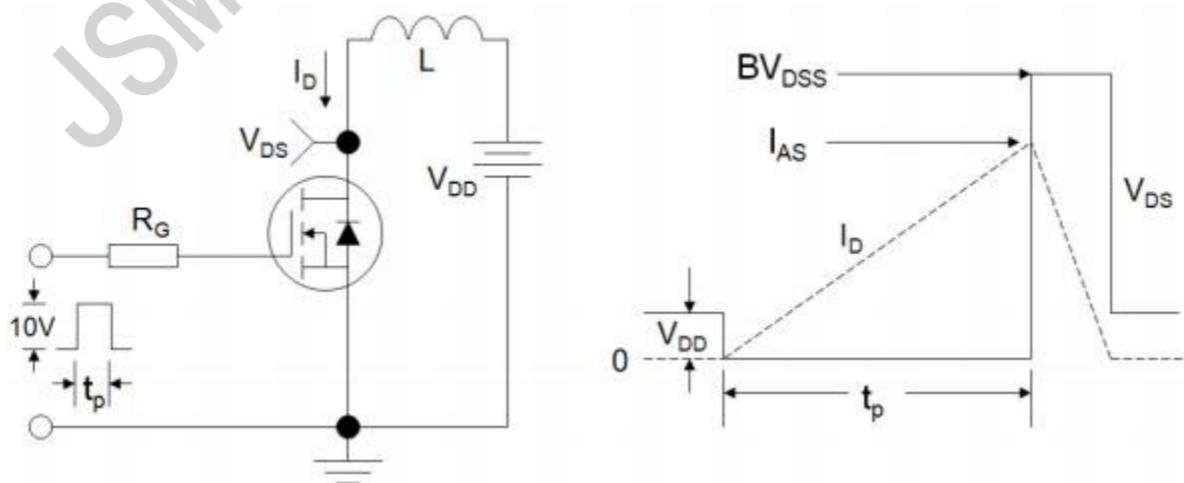
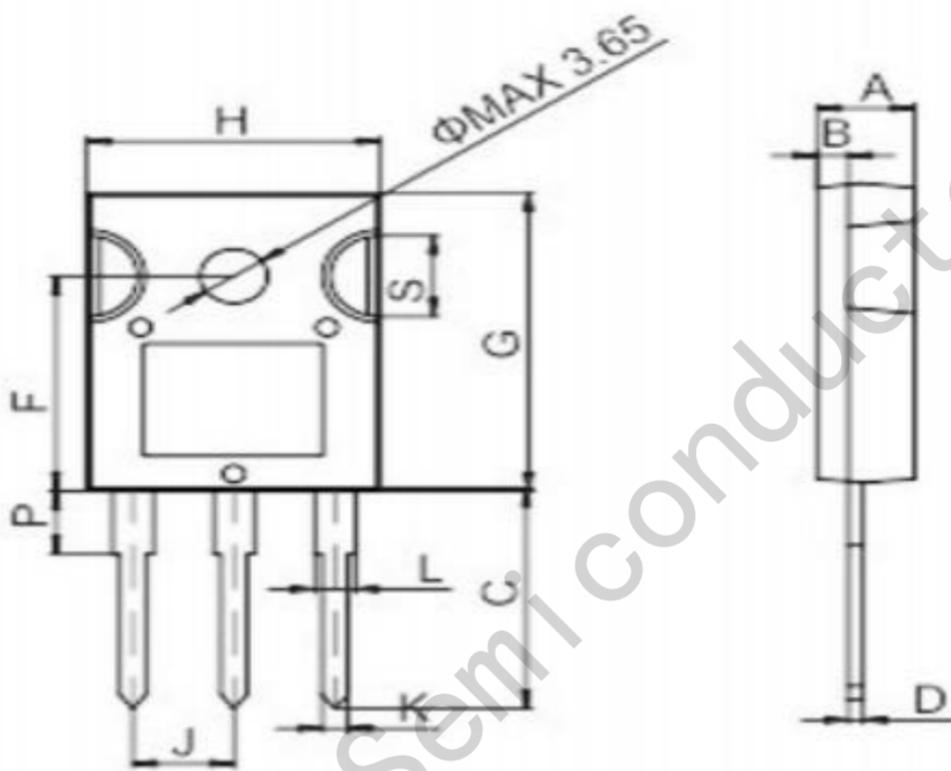


Figure A: Gate Charge Test Circuit and Waveform

Figure B: Resistive Switching Test Circuit and Waveform

Figure C: Unclamped Inductive Switching Test Circuit and Waveform


TO-247



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.9		5.4	0.193		0.213
B	1.6		2.0	0.063		0.079
C	14.35		15.4	0.565		0.606
D	0.5		0.8	0.020		0.031
F	14.4		15.1	0.567		0.594
G	19.7		20.6	0.775		0.811
H	15.4		16.2	0.606		0.638
J	5.3		5.6	0.209		0.220
K	1.3		1.5	0.051		0.059
L	2.8		3.3	0.110		0.130
P	3.7		4.2	0.146		0.165
S	5.35		5.65	0.211		0.222

单击下面可查看定价，库存，交付和生命周期等信息

[>>JSMSEMI\(杰盛微\)](#)